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S B F

## \*\* CONTINUING DATA \*\*\*\*\*

This application is a DIV of 10/005,355 12/07/2001 PAT 6,710,383

S B F

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

JAPAN 2000-375610 12/11/2001

S B F

## IF REQUIRED, FOREIGN FILING LICENSE GRANTED

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Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY	SHEETS DRAWING	TOTAL CLAIMS	INDEPENDENT CLAIMS
35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance	JAPAN	7	12	2
Verified and Acknowledged	Examiner's Signature <i>Ad O B</i>	Initials S B F		

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METHOD OF MAKING A MISFET SEMICONDUCTOR DEVICE HAVING  
 TITLE A HIGH DIELECTRIC CONSTANT INSULATING FILM WITH  
 Semiconductor device and process for producing the same. **TAPERED END PORTIONS**

FILING FEE	FEES: Authority has been given in Paper	<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees ( Filing ) <input type="checkbox"/> 1.17 Fees ( Processing Ext. of
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